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<u>Diodes Incorporated</u> <u>DMG2307L-7</u>

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Datasheet of DMG2307L-7 - MOSFET P-CH 30V 2.5A SOT-23

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DMG2307L

P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = +25°C
	90mΩ @ V _{GS} = -10V	-3.8A
-30V	134mΩ @ V _{GS} = -4.5V	-3.1A

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 standards for High Reliability

Description and Applications

This MOSFET has been designed to minimize the on-state resistance $(R_{DS(on)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

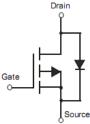
- General Purpose Interfacing Switch
- Power Management Functions
- Load Switch for Portable Devices

Mechanical Data

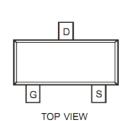
- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See diagram
- Terminals: Finish Matte Tin annealed over Copper leadframe.
 Solderable per MIL-STD-202, Method 208
- Weight: 0.08 grams (approximate)







Internal Schematic



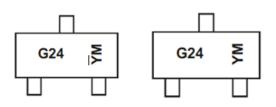
Ordering Information (Notes 4 & 5)

	Part Number	Part Number Compliance		Packaging
	DMG2307L-7	MG2307L-7 Standard SOT-23		3000Tape & Reel
ı	DMG2307LQ-7	Automotive	SOT-23	3000Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_compliance_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



G24 = Product Type Marking Code $\underline{Y}M$ = Date Code Marking for SAT (Shanghai Assembly/ Test site) $\underline{Y}M$ = Date Code Marking for CAT (Chengdu Assembly/ Test site) $\underline{Y}M$ = $\underline{Y}M$ = Year (ex: A = 2013) \underline{M} = Month (ex: 9 = September)

Chengdu A/T Site

Shanghai A/T Site

Date Code Key

Year	2009	2010	20	11	2012	2013	2014	2015	20	16	2017	2018
Code	W	Х	`	1	Z	Α	В	С	[)	Е	F
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Drain-Source Voltage		V _{DSS}	-30	V	
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = -10V	Steady State	T _A = +25°C T _A = +70°C	I _D	-2.5 -2.0	А
Continuous Drain Current (Note 7) V _{GS} = -10V	Steady State	T _A = +25°C T _A = +70°C	I _D	-3.8 -3.0	А
Continuous Drain Current (Note 7) V _{GS} = -10V	t ≦10sec	T _A = +25°C T _A = +70°C	I _D	-4.6 -3.6	А
Continuous Drain Current (Note 7) V _{GS} = -4.5V	Steady State	T _A = +25°C T _A = +70°C	I _D	-3.1 -2.5	А
Pulsed Drain Current (Note 7)			I _{DM}	-20	Α

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 6)	P_{D}	0.76	W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{ heta JA}$	159	°C/W
Total Power Dissipation (Note 7)	P_{D}	1.36	W
Thermal Resistance, Junction to Ambient (Note 7)	$R_{ heta JA}$	94	°C/W
Total Power Dissipation (Note 7) $t \le 10$ sec	P_{D}	1.9	W
Thermal Resistance, Junction to Ambient (Note 7) $t \le 10$ sec	$R_{ heta JA}$	65.8	°C/W
Operating and Storage Temperature Range	$T_{J_i}T_{STG}$	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)					-			
Drain-Source Breakdown Voltage		BV _{DSS}	-30	_	_	٧	$V_{GS} = 0V$, $I_{D} = -250\mu A$	
Zero Gate Voltage Drain Current	@T _C = +25°C	I _{DSS}	ı	_	-1.0	μΑ	$V_{DS} = -30V, V_{GS} = 0V$	
Gate-Source Leakage		I _{GSS}	-	-	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)								
Gate Threshold Voltage		$V_{GS(th)}$	-1.0	_	-3.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	
Static Drain-Source On-Resistance		D	I	70	90	mΩ	$V_{GS} = -10V, I_D = -2.5A$	
Static Dialii-Source Oil-Resistance		R _{DS} (ON)	ı	105	134	11152	$V_{GS} = -4.5V$, $I_D = -2.5A$	
Forward Transfer Admittance		Y _{fs}	-	4.8	_	S	$V_{DS} = -10V$, $I_{D} = -2.5A$	
Diode Forward Voltage (Note 7)		V_{SD}	_	-0.75	-1.0	V	$V_{GS} = 0V, I_{S} = -1A$	
DYNAMIC CHARACTERISTICS (Note 9)								
Input Capacitance		C _{iss}	_	371.3	_	pF	15)()(
Output Capacitance		Coss	ı	51.3	-	pF	$V_{DS} = -15V, V_{GS} = 0V,$ - f = 1.0MHz	
Reverse Transfer Capacitance		C _{rss}	-	45.9	-	pF	1 - 1.0WH12	
Gate Resistance		R_g	_	17	_	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = -4.5V)		Qg	_	4.0	_	nC		
Total Gate Charge (V _{GS} = -10V)		Qg	_	8.2	_	nC	$V_{GS} = -10V, V_{DS} = -15V,$	
Gate-Source Charge		Q _{gs}	_	0.9	-	nC	$I_D = -3A$	
Gate-Drain Charge		Q_{qd}	-	1.2	_	nC		
Turn-On Delay Time		t _{D(on)}	_	4.8	_	ns	45)/)/ 40)/	
Turn-On Rise Time		t _r	_	7.3	_	ns	$V_{DS} = -15V, V_{GS} = -10V,$	
Turn-Off Delay Time		t _{D(off)}	-	22.4	_	ns	$R_L = 15\Omega$, $R_G = 6\Omega$,	
Turn-Off Fall Time		t _f	ı	13.4	-	ns	$I_D = -1A$	

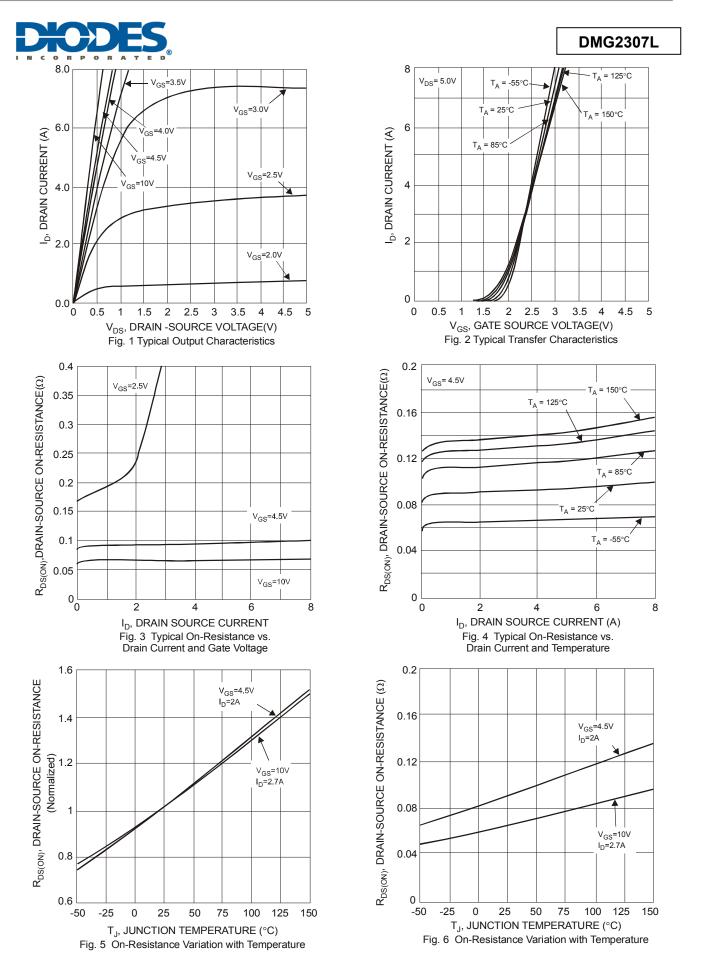
Notes: 6. Device mounted on FR-4 PCB, with minimum recommended pad layout.

- 7. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.
- 8. Short duration pulse test used to minimize self-heating effect.

Guaranteed by design. Not subject to product testing.

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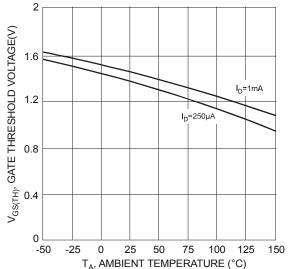
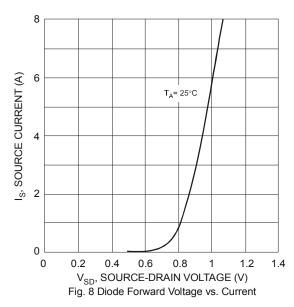
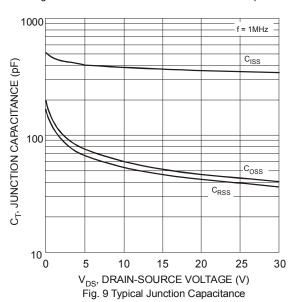


Fig. 7 Gate Threshold Variation vs. Ambient Temperature





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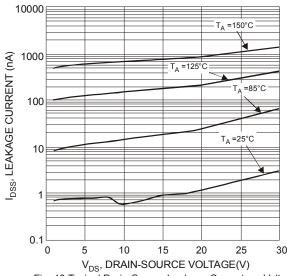
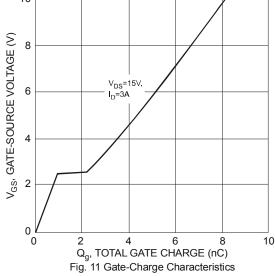


Fig. 10 Typical Drain-Source Leakage Current vs. Voltage



100 R_{DS(ON)} I_D(A) @P_W=1ms -I_D(A) @ 10 -I_D, DRAIN CURRENT (A) -I_D(A) @P T_{J(MAX)} = 150°C T_A = 25°C Single Pulse (A) @P_w=10m 0.01 10 100 -V_{DS}, DRAIN-SOURCE VOLTAGE (V) Fig. 12 SOA, Safe Operation Area

DMG2307L Document number: DS35414 Rev. 3 - 2

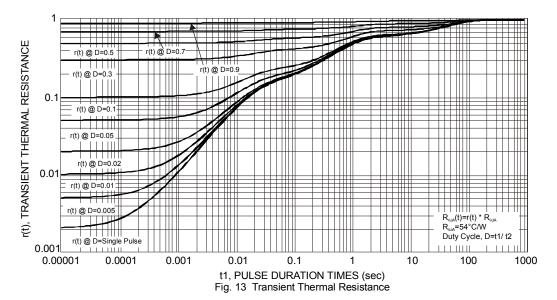
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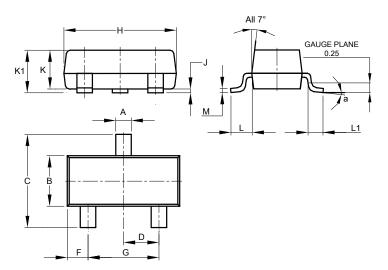


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Package Outline Dimensions

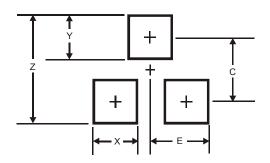
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23							
Dim	Dim Min		Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
C	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78 2.05		1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
١	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
α	α 8°						
All	Dimens	ions in	mm				

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35



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